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	Application No.	Applicant(s)	
Modice of Allered 194	10/001,977	TANIMOTO ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Pamela E Perkins	2822	
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communicatio GHTS. This application is subject t	pplication. If not include n will be mailed in due	ed course. <b>THIS</b>
1. $\boxtimes$ This communication is responsive to <u>the amendment received</u>	ved on 20 February 2004.		
2. ☑ The allowed claim(s) is/are <u>1-3 and 5-16</u> .			
3. The drawings filed on <u>05 December 2001</u> are accepted by	the Examiner.		
4.  Acknowledgment is made of a claim for foreign priority un a)  All b)  Some* c)  None of the:  1.  Certified copies of the priority documents have  2.  Certified copies of the priority documents have  3.  Copies of the certified copies of the priority documents have  International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" on oted below. Failure to timely comply will result in ABANDONMITHIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  5.  A SUBSTITUTE OATH OR DECLARATION must be submiting INFORMAL PATENT APPLICATION (PTO-152) which give  (a)  including changes required by the Notice of Draftsperson  1)  hereto or 2)  to Paper No./Mail Date  (b)  including changes required by the attached Examiner's  Paper No./Mail Date  Identifying indicia such as the application number (see 37 CFR 1.6 each sheet. Replacement sheet(s) should be labeled as such in the  paper No./Mail Date  DEPOSIT OF and/or INFORMATION about the depose attached Examiner's comment regarding REQUIREMENT F	been received. been received in Application No cuments have been received in this of this communication to file a reply ENT of this application.  tted. Note the attached EXAMINER is reason(s) why the oath or declara t be submitted. on's Patent Drawing Review ( PTO- Amendment / Comment or in the Comment or in the Comment of the drawing header according to 37 CFR 1.121( sit of BIOLOGICAL MATERIAL I	national stage applical complying with the recomplying with the recomply	quirements OTICE OF
Attachment(s)  1. ☑ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	8.  Examiner's Stateme	(PTO-413), te <u>2/11/04</u> ment/Comment	wance

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# **DETAILED ACTION**

This office action is in response to the filing of the request for reconsideration received on 20 February 2004. Claims 1-3 and 5-22 are pending; claims 17-22 have been withdrawn from consideration.

# **EXAMINER'S AMENDMENT**

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

Cancel claims 17-22.

# Allowable Subject Matter

Claims 1-3 and 5-16 are allowed.

#### Reasons for Allowance

The following is an examiner's statement of reasons for allowance: prior art does not anticipate, teach, or suggest a method of manufacturing a semiconductor device, where a semiconductor element is formed in a semiconductor active region the semiconductor active region being in an electrically floating state, calculating a generation rate of electron hole pairs caused by impact ionization in said semiconductor

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element; calculating a volume integral of said generation rate of electron hole pairs in an area where the impact ionization is caused; evaluating time-dependent variations of electrical characteristics of said semiconductor element on the basis of said volume integral; and manufacturing a semiconductor device based on results of the evaluating step.

Agarwal et al. (5,510,630) disclose a method of manufacturing a semiconductor device where a semiconductor element is formed in a semiconductor active region and calculating the generation rate of electron hole and a time integral of physical quantities. Agarwal et al. further disclose manufacturing a semiconductor device on the basis of the results. However, Agarwal et al. do not disclose, anticipate, teach, or suggest calculating a volume integral of the generation rate of electron hole pairs in an area where the impact ionization is caused and evaluating time-dependent variations of electrical characteristics of the semiconductor element on the basis of the volume integral and manufacturing a semiconductor device based on results of the evaluating step.

Huth (5,021,854) discloses a method of manufacturing a semiconductor device where a semiconductor element is formed in a semiconductor active region, calculating the generation rate of electron hole pairs caused by impact ionization and evaluating time-dependent variations of electrical characteristics of the semiconductor element (col. 1, lines 8-38; col. 9, lines 37-55). However, Huth does not disclose, anticipate, teach or suggest the semiconductor active region being in an electrically floating state; calculating a volume integral of said generation rate of electron hole pairs in an area

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where the impact ionization is caused; evaluating time-dependent variations of electrical characteristics of said semiconductor element on the basis of said volume integral; and manufacturing a semiconductor device based on results of the evaluating step.

The prior art made of record in this action does not anticipate, teach, or suggest a method of manufacturing a semiconductor device, where a semiconductor element is formed in a semiconductor active region the semiconductor active region being in an electrically floating state, calculating a generation rate of electron hole pairs caused by impact ionization in said semiconductor element; calculating a volume integral of said generation rate of electron hole pairs in an area where the impact ionization is caused; evaluating time-dependent variations of electrical characteristics of said semiconductor element on the basis of said volume integral; and manufacturing a semiconductor device based on results of the evaluating step.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

# Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Pamela E Perkins whose telephone number is (571) 272-1840. The examiner can normally be reached on Monday thru Friday, 9:00am to 5:30pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

PEP

AMIR ZARABIAN
PERMISORY PATENT EXAMINER
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